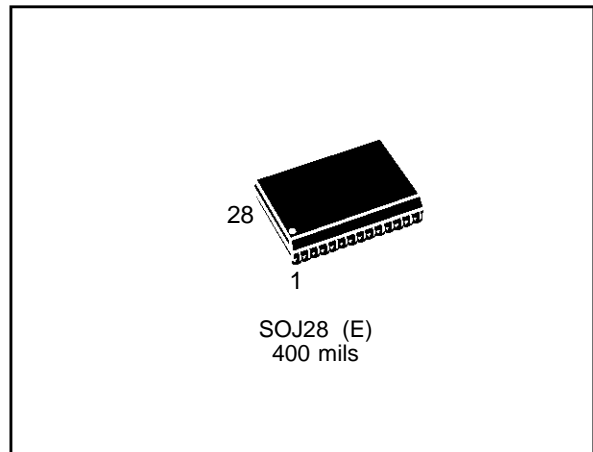


**1 Megabit (256K x 4) VERY FAST SRAM  
WITH OUTPUT ENABLE**

- 256K x 4 VERY FAST SRAM with OUTPUT ENABLE
- EQUAL CYCLE and ACCESS TIMES: 15, 20ns
- LOW V<sub>CC</sub> DATA RETENTION: 2V
- TRI-STATE COMMON I/O
- JEDEC PLASTIC SOJ, 400 mil PACKAGE



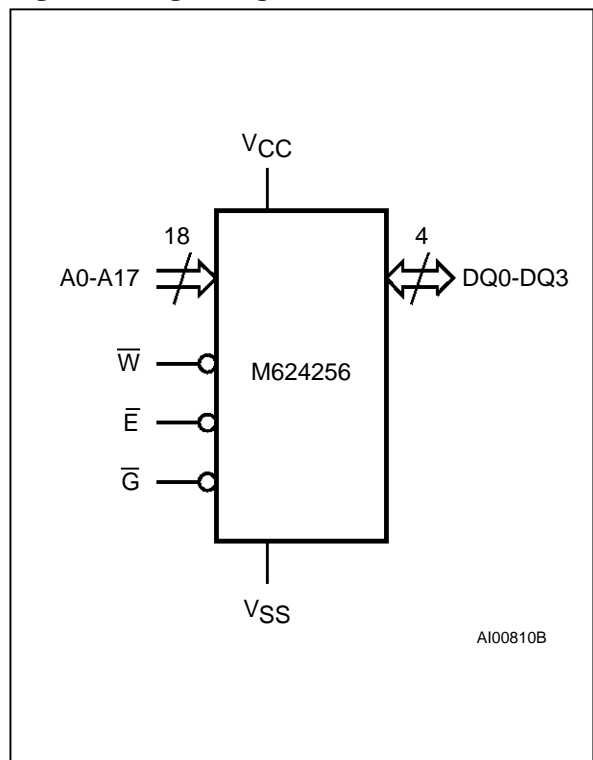
**DESCRIPTION**

The M624256 is a 1 Megabit (1,048,567 bit) Fast CMOS SRAM, organized as 262,144 words by 4 bits. It is fabricated using SGS-THOMSON's Advanced, low power, high performance, CMOS technology. The device features fully static operation requiring no external clocks or timing strobes, with equal address access and cycle times. It requires a single 5V ± 10% supply, and all inputs and outputs are TTL compatible.

**Table 1. Signal Names**

A0 - A17	Address Inputs
DQ0 - DQ3	Data Inputs / Outputs
$\bar{E}$	Chip Enable
$\bar{G}$	Output Enable
$\bar{W}$	Write Enable
V <sub>CC</sub>	Supply Voltage
V <sub>SS</sub>	Ground

**Figure 1. Logic Diagram**



**Table 2. Absolute Maximum Ratings <sup>(1)</sup>**

Symbol	Parameter	Value	Unit
T <sub>A</sub>	Ambient Operating Temperature	0 to 70	°C
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C
V <sub>IO</sub> <sup>(2)</sup>	Input or Output Voltages	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>CC</sub>	Supply Voltage	-0.5 to 7	V
I <sub>O</sub> <sup>(3)</sup>	Output Current	20	mA
P <sub>D</sub>	Power Dissipation	1	W

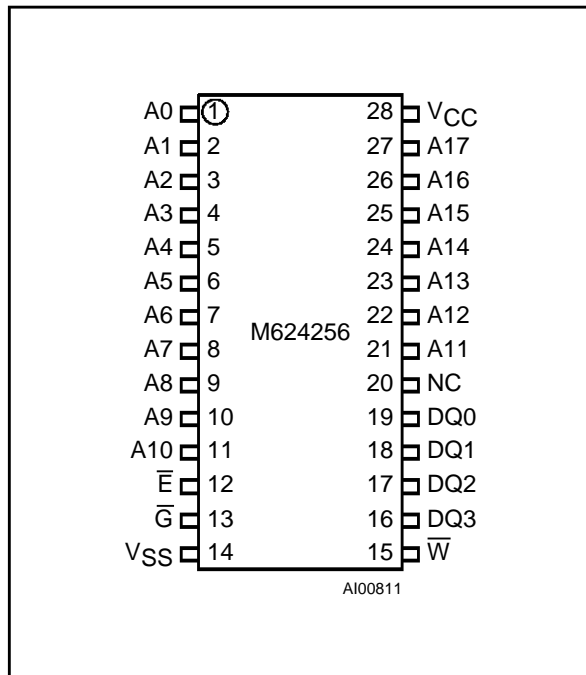
**Notes:** 1. Except for the rating "Operating Temperature Range" stresses above those listed in the Table "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods may affect device reliability. Refer also to the SGS-THOMSON SURE Program and other relevant quality documents.  
 2. Up to a maximum operating V<sub>CC</sub> of 5.5V only.  
 3. One output at a time, not to exceed 1 second duration.

**Table 3. Operating Modes**

Mode	$\bar{E}$	$\bar{W}$	$\bar{G}$	DQ0-DQ3	Power
Read	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IH</sub>	Hi-Z	Active
Read	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IL</sub>	Data Output	Active
Write	V <sub>IL</sub>	V <sub>IL</sub>	X	Data Input	Active
Deselect	V <sub>IH</sub>	X	X	Hi-Z	Standby

**Note:** X = V<sub>IH</sub> or V<sub>IL</sub>.

**Figure 2. SOJ Pin Connections**



**Warning:** NC = Not Connected.

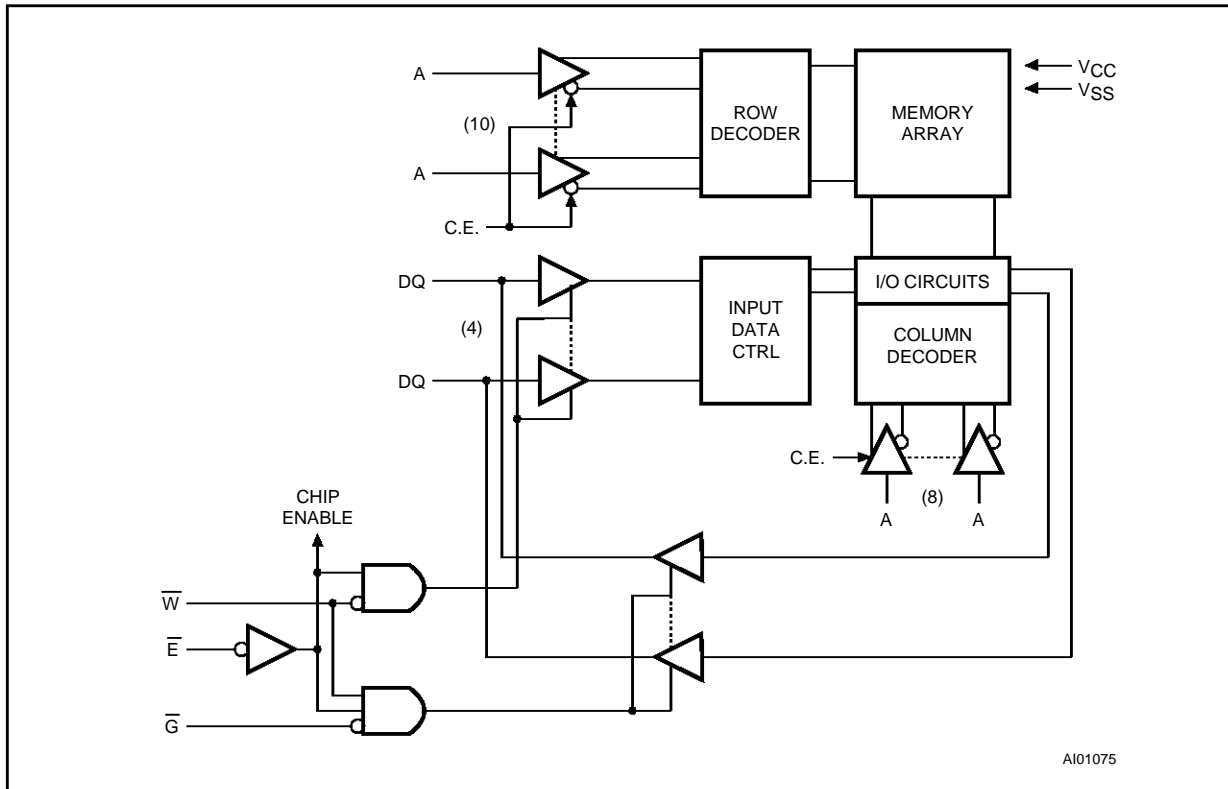
**READ MODE**

The M624256 is in the Read mode whenever Write Enable ( $\bar{W}$ ) is High with Output Enable ( $\bar{G}$ ) Low, and Chip Enable ( $\bar{E}$ ) asserted. This provides access to data from four of the 1,048,576 locations in the static memory array, specified by the 18 address inputs. Valid data will be available at the four output pins within t<sub>AVQV</sub> after the last stable address, providing  $\bar{G}$  is Low and  $\bar{E}$  is Low. If Chip Enable or Output Enable access times are not met, data access will be measured from the limiting parameter (t<sub>ELQV</sub> or t<sub>GLQV</sub>) rather than the address. Data out may be indeterminate at t<sub>ELQX</sub> and t<sub>GLQX</sub>, but data lines will always be valid at t<sub>AVQV</sub>.

**WRITE MODE**

The M624256 is in the Write mode whenever the  $\bar{W}$  and  $\bar{E}$  pins are Low. Either the Chip Enable input ( $\bar{E}$ ) or the Write Enable input ( $\bar{W}$ ) must be de-asserted during Address transitions for subsequent write cycles. Write begins with the concurrence of Chip Enable being active with  $\bar{W}$  Low. Therefore, address setup time is referenced to Write Enable and Chip Enable as t<sub>AVWL</sub> and t<sub>AVEL</sub> respectively,

Figure 3. Block Diagram



**WRITE MODE** (cont'd)

and is determined by the latter occurring edge. The Write cycle can be terminated by the earlier rising edge of  $\bar{E}$  or  $\bar{W}$ .

If the Output is enabled ( $\bar{E} = \text{Low}$  and  $\bar{G} = \text{Low}$ ), then  $\bar{W}$  will return the outputs to high impedance within  $t_{WLQZ}$  of its falling edge. Care must be taken to avoid bus contention in this type of operation. Data input must be valid for  $t_{DVWH}$  before the rising edge of Write Enable, or for  $t_{DVEH}$  before the rising edge of  $\bar{E}$  whichever occurs first, and remain valid for  $t_{WHDX}$  or  $t_{EHDX}$ .

**OPERATIONAL MODE**

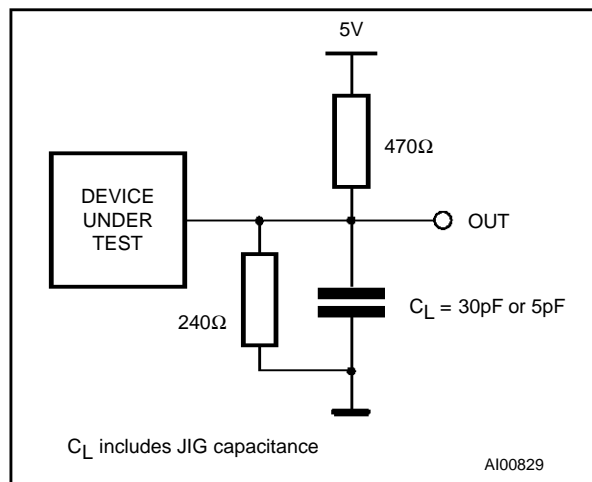
The M624256 has a Chip Enable power down feature which invokes an automatic standby mode whenever Chip Enable is de-asserted ( $\bar{E} = \text{High}$ ). An Output Enable ( $\bar{G}$ ) signal provides a high speed tri-state control, allowing fast read/write cycles to be achieved with the common I/O data bus. Operational modes are determined by device control inputs  $\bar{W}$  and  $\bar{E}$  as summarized in the Operating Modes table.

**AC MEASUREMENT CONDITIONS**

Input Rise and Fall Times	$\leq 1.5\text{ns}$
Input Pulse Voltages	0 to 3V
Input and Output Timing Ref. Voltages	1.5V

Note that Output Hi-Z is defined as the point where data is no longer driven.

Figure 4. AC Testing Load Circuit



**Table 4. Capacitance** <sup>(1)</sup> ( $T_A = 25\text{ }^\circ\text{C}$ ,  $f = 1\text{ MHz}$ )

Symbol	Parameter	Test Condition	Min	Max	Unit
$C_{IN}$ <sup>(2)</sup>	Input Capacitance on all pins (except DQ)	$V_{IN} = 0V$		8	pF
$C_{OUT}$ <sup>(3)</sup>	Output Capacitance	$V_{OUT} = 0V$		8	pF

**Notes:** 1. Sampled only, not 100% tested  
 2. Except DQ0-DQ3  
 3. Outputs deselected

**Table 5. DC Characteristics** ( $T_A = 0\text{ to }70\text{ }^\circ\text{C}$ ,  $V_{CC} = 5V \pm 10\%$ )

Symbol	Parameter	Test Condition	Min	Max	Unit
$I_{LI}$	Input Leakage Current	$0V \leq V_{IN} \leq V_{CC}$		$\pm 1$	$\mu\text{A}$
$I_{LO}$	Output Leakage Current	$0V \leq V_{OUT} \leq V_{CC}$		$\pm 5$	$\mu\text{A}$
$I_{CC1}$ <sup>(1)</sup>	Supply Current	$V_{CC} = 5.5V, (-15)$		175	mA
		$V_{CC} = 5.5V, (-20)$		140	mA
$I_{CC2}$ <sup>(2)</sup>	Supply Current (Standby) TTL	$V_{CC} = 5.5V, \bar{E} = V_{IH}, f = 0$		30	mA
$I_{CC3}$ <sup>(3)</sup>	Supply Current (Standby) CMOS	$V_{CC} = 5.5V, \bar{E} \geq V_{CC} - 0.2V, f = 0$		4	mA
$V_{IL}$	Input Low Voltage		-0.3	0.8	V
$V_{IH}$	Input High Voltage		2.2	$V_{CC} + 0.3$	V
$V_{OL}$	Output Low Voltage	$I_{OL} = 8\text{mA}$		0.4	V
$V_{OH}$	Output High Voltage	$I_{OH} = -4\text{mA}$	2.4		V

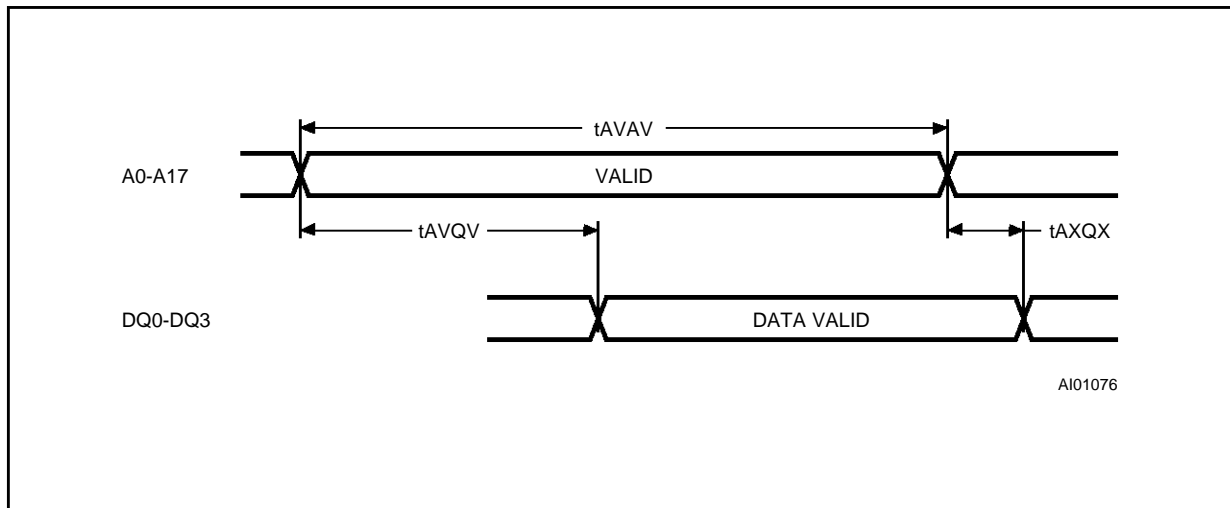
**Notes:** 1. Average AC current, Outputs open, cycling at  $t_{AVAV}$  minimum  
 2. All other Inputs at  $V_{IL} \leq 0.8V$  or  $V_{IH} \geq 2.2V$   
 3. All other Inputs at  $V_{IL} \leq 0.2V$  or  $V_{IH} \geq V_{CC} - 0.2V$

**Table 6. Read and Standby Modes AC Characteristics** ( $T_A = 0$  to  $70^\circ\text{C}$ ,  $V_{CC} = 5\text{V} \pm 10\%$ )

Symbol	Parameter	M624256				Unit
		-15		-20		
		Min	Max	Min	Max	
$t_{AVAV}$	Read Cycle Time	15		20		ns
$t_{AVQV}^{(1)}$	Address Valid to Output Valid		15		20	ns
$t_{ELQV}^{(1)}$	Chip Enable Low to Output Valid		15		20	ns
$t_{GLQV}^{(1)}$	Output Enable Low to Output Valid		7		8	ns
$t_{ELQX}^{(2)}$	Chip Enable Low to Output Transition	2		2		ns
$t_{GLQX}^{(2)}$	Output Enable Low to Output Transition	0		0		ns
$t_{EHQZ}^{(2)}$	Chip Enable High to Output Hi-Z	0	8	0	10	ns
$t_{GHQZ}^{(2)}$	Output Enable High to Output Hi-Z	0	7	0	9	ns
$t_{AXQX}^{(1)}$	Address Transition to Output Transition	3		3		ns
$t_{PU}^{(3)}$	Chip Enable Low to Power Up	0		0		ns
$t_{PD}^{(3)}$	Chip Enable High to Power Down		15		20	ns

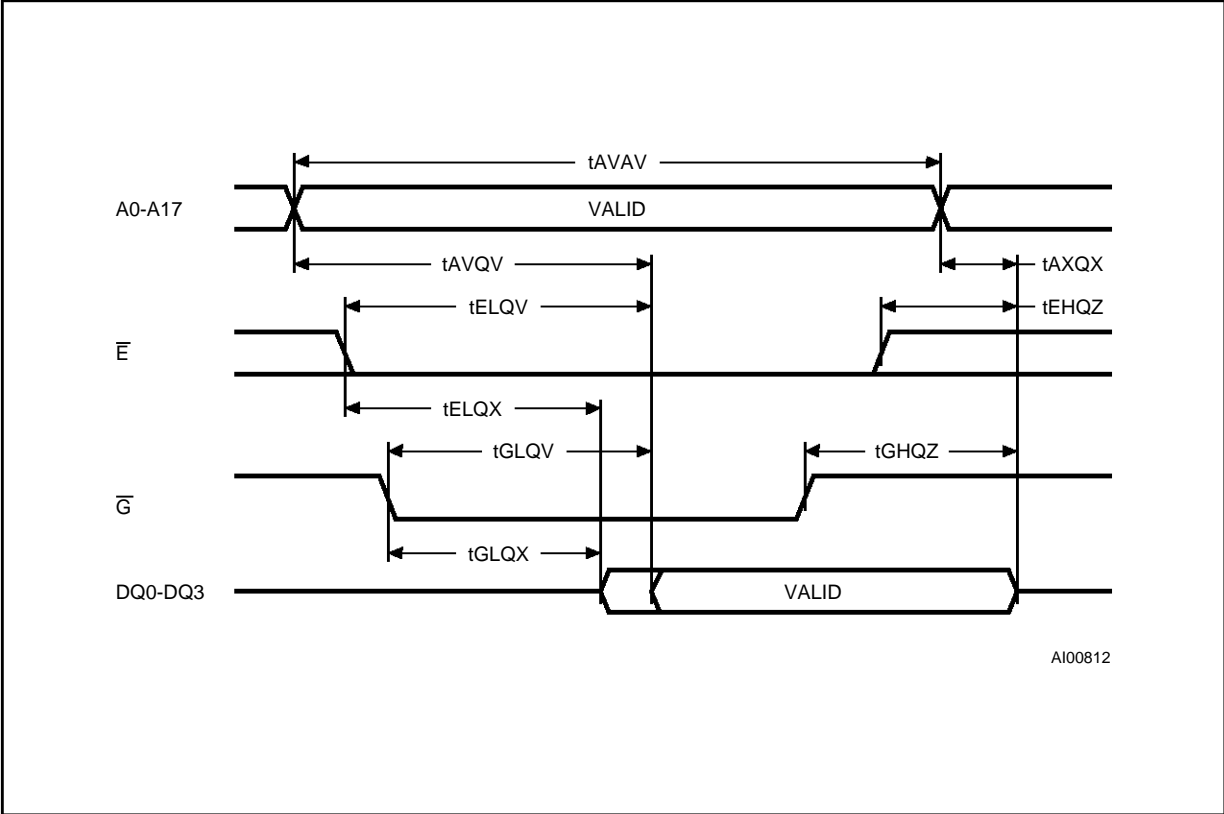
Notes: 1.  $C_L = 30\text{pF}$  (see Figure 4)  
 2.  $C_L = 5\text{pF}$  (see Figure 4)  
 3. Guaranteed but not tested (see Figure 7)

**Figure 5. Address Controlled, Read Mode AC Waveforms**



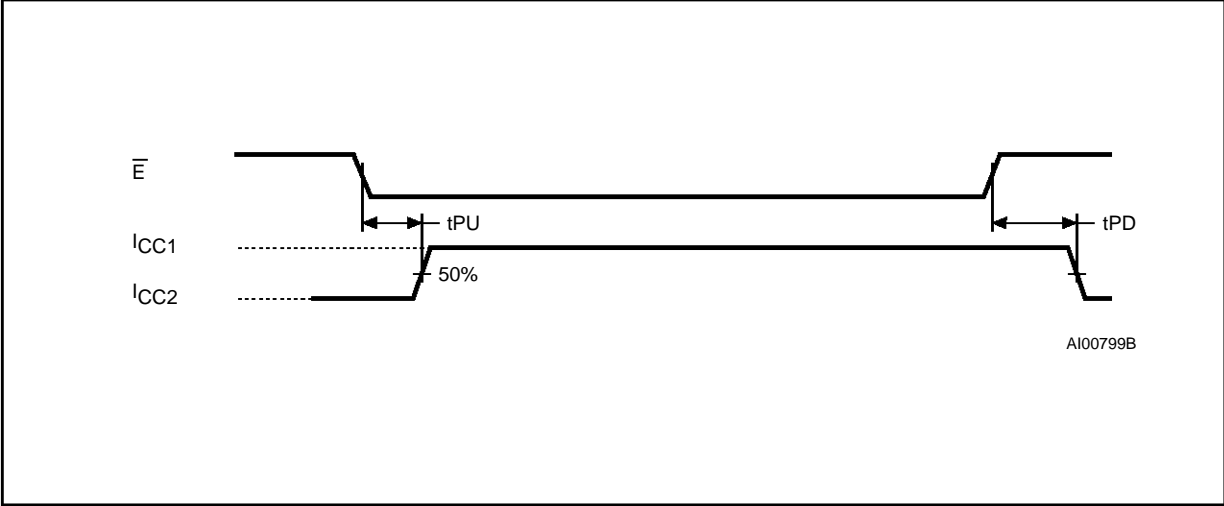
Note: ( $\bar{E}$ ) = Low, ( $\bar{G}$ ) = Low, ( $\bar{W}$ ) = High

Figure 6. Chip Enable or Output Enable Controlled, Read Mode AC Waveforms



Note: Write Enable ( $\bar{W}$ ) = High

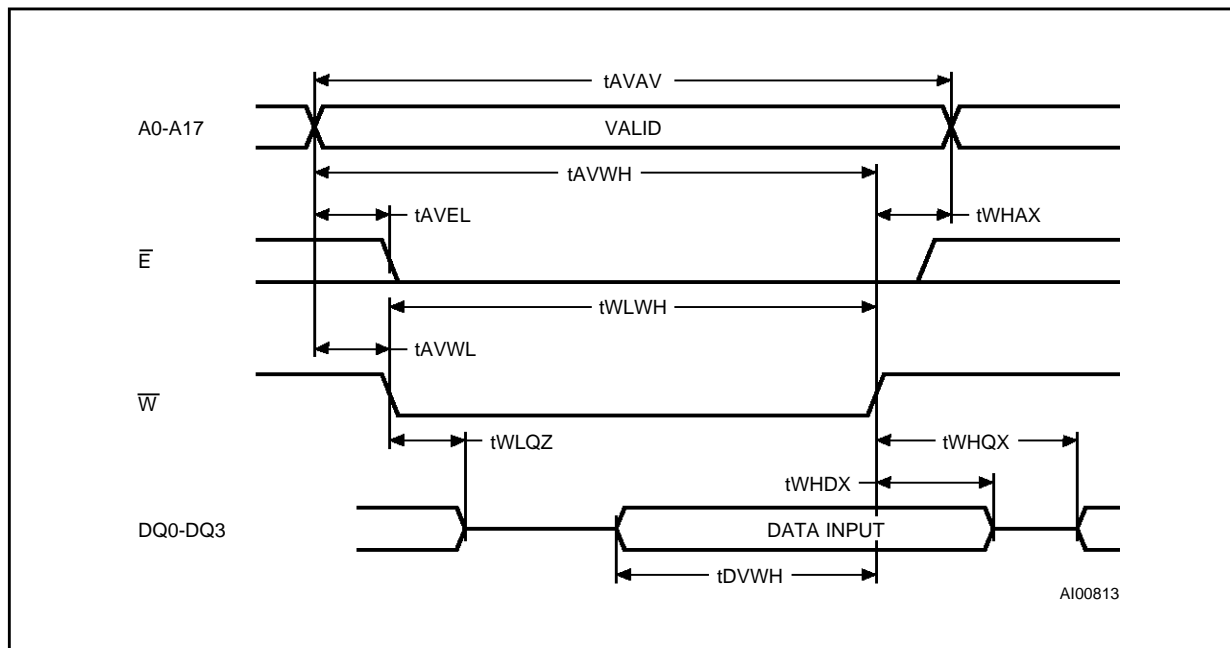
Figure 7. Standby Mode AC Waveforms



**Table 7. Write Mode AC Characteristics** ( $T_A = 0$  to  $70^\circ\text{C}$ ,  $V_{CC} = 5\text{V} \pm 10\%$ )

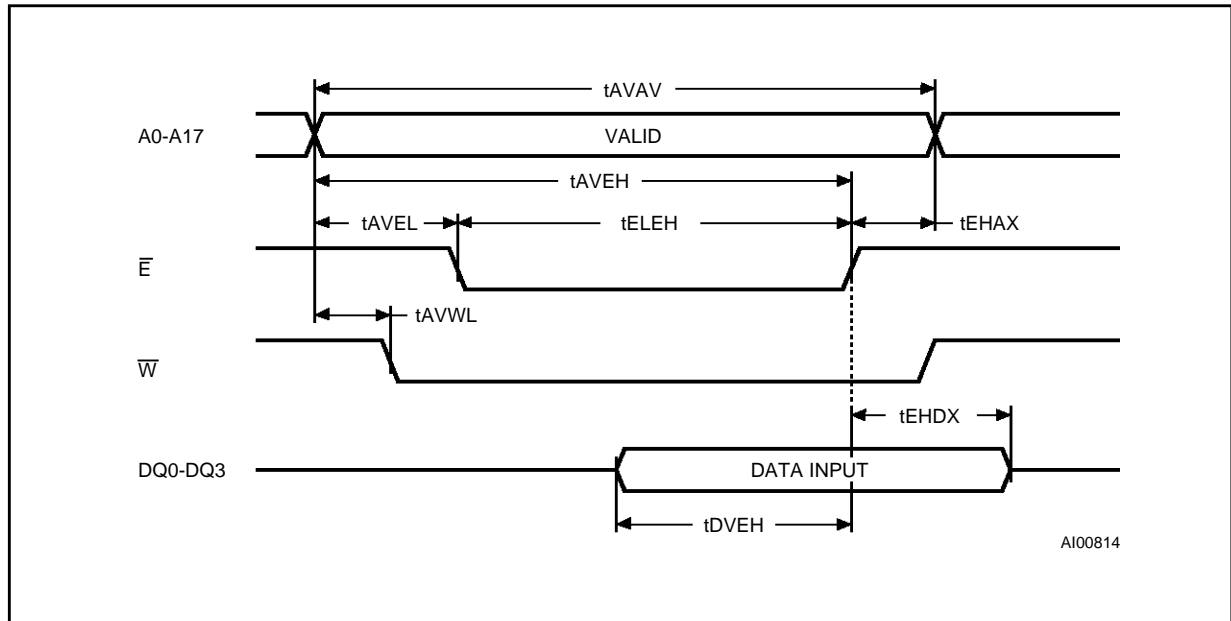
Symbol	Parameter	M624256				Unit
		-15		-20		
		Min	Max	Min	Max	
$t_{AVAV}$	Write Cycle Time	15		20		ns
$t_{AVWL}$	Address Valid to Write Enable Low	0		0		ns
$t_{AVWH}$	Address Valid to Write Enable High	10		12		ns
$t_{AVEH}$	Address Valid to Chip Enable High	11		12		ns
$t_{WLWH}$	Write Enable Pulse Width	10		12		ns
$t_{WHAX}$	Write Enable High to Address Transition	0		0		ns
$t_{WHDX}$	Write Enable High to Input Transition	0		0		ns
$t_{EHDX}$	Chip Enable High to Input Transition	0		0		ns
$t_{WHQX}^{(1)}$	Write Enable High to Output Transition	0		0		ns
$t_{WLQZ}^{(1)}$	Write Enable Low to Output Hi-Z	0	8	0	10	ns
$t_{AVEL}$	Address Valid to Chip Enable Low	0		0		ns
$t_{ELEH}$	Chip Enable Low to Chip Enable High	11		12		ns
$t_{EHAX}$	Chip Enable High to Address Transition	0		0		ns
$t_{DVWH}$	Input Valid to Write Enable High	8		12		ns
$t_{DVEH}$	Input Valid to Chip Enable High	8		12		ns

Note: 1.  $C_L = 5\text{pF}$  (see Figure 4)

**Figure 8. Write Enable Controlled, Write AC Waveforms**

Note: Output Enable ( $\bar{G}$ ) = Low

Figure 9. Chip Enable Controlled, Write AC Waveforms



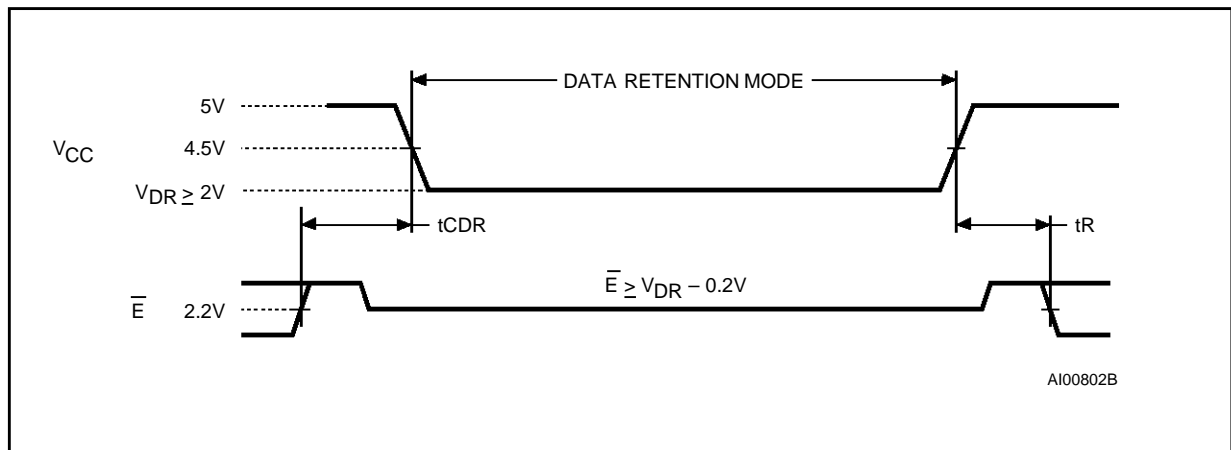
Note: Output Enable ( $\bar{G}$ ) = High

Table 8. Low  $V_{CC}$  Data Retention Characteristics ( $T_A = 0$  to  $70^\circ\text{C}$ ,  $V_{CC} = 2\text{V}$  to  $4.5\text{V}$ )

Symbol	Parameter	Test Condition	Min	Max	Unit
$I_{CCDR}^{(1)}$	Supply Current (Data Retention)	$V_{CC} = 3\text{V}, \bar{E} \geq V_{CC} - 0.2\text{V}, f = 0$		500	$\mu\text{A}$
$V_{DR}^{(1)}$	Supply Voltage (Data Retention)	$\bar{E} \geq V_{CC} - 0.2\text{V}, f = 0$	2	4.5	V
$t_{CDR}^{(1,2)}$	Chip Disable to Power Down	$\bar{E} \geq V_{CC} - 0.2\text{V}, f = 0$	0		ns
$t_R^{(2)}$	Operation Recovery Time			$t_{AVAV}$	ns

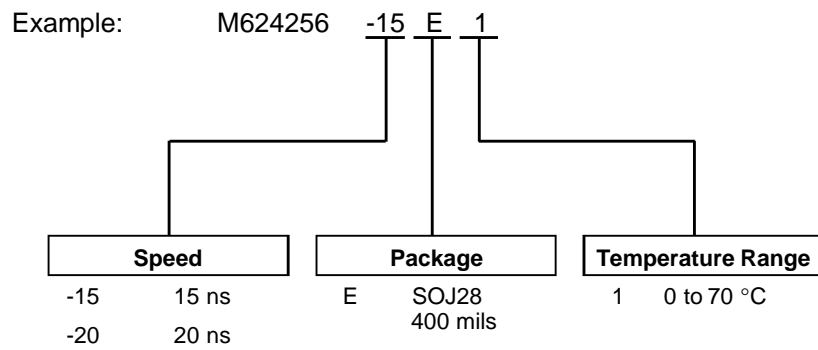
Notes: 1. All other inputs  $V_{IH} \geq V_{CC} - 0.2\text{V}$  or  $V_{IL} \leq 0.2\text{V}$   
 2. See Figure 8 for measurement points. Guaranteed but not tested

Figure 8. Low  $V_{CC}$  Data Retention AC Waveforms





## ORDERING INFORMATION SCHEME

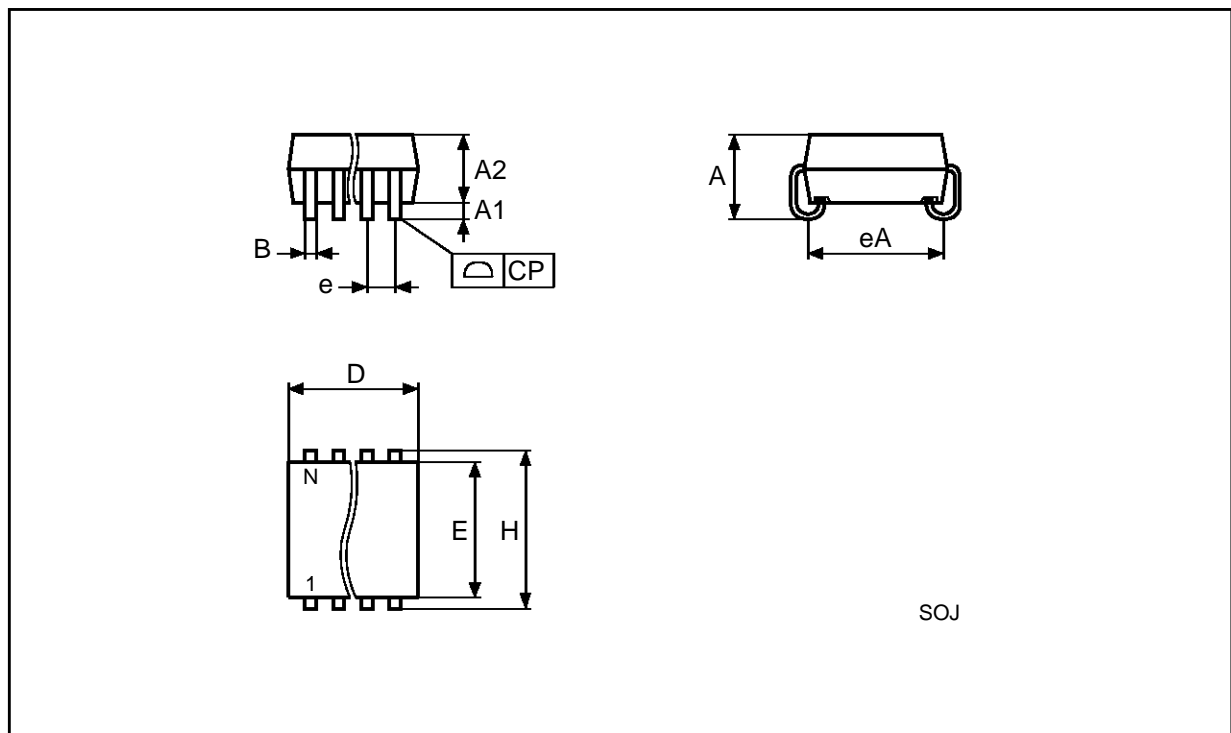


For a list of available options (Speed, Package etc... ) refer to the current Memory Shortform catalogue.  
For further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.

**SOJ28 - 28 lead Plastic Small Outline J-lead, 400 mils**

Symb	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A		3.33	3.68		0.131	0.145
A1		1.14	1.40		0.045	0.055
A2		2.18	2.29		0.086	0.090
B		0.38	0.51		0.015	0.020
D		17.81	18.06		0.701	0.711
E		10.03	10.29		0.395	0.405
e	1.27	-	-	0.050	-	-
eA		9.14	9.65		0.360	0.380
H		11.05	11.30		0.435	0.445
N	28			28		
CP			0.10			0.004

SOJ28



Drawing is not to scale.

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